

## IN THE CLAIMS

1. - 28. (Cancelled)

29. (Currently Amended) An electron-emitting device manufacturing method comprising:

a gas removal step of removing a gas dissolved in a liquid containing a formation material of an electroconductive film in which an electron-emitting area is to be formed;

a temperature adjusting step of adjusting a temperature of the liquid from which the gas is removed;

a droplet discharge step of discharging droplets of which the temperature is adjusted by droplet discharge means in an ink jet manner while controlling relative positions of the droplet discharge means for discharging droplets of the liquid and a substrate on which the electroconductive film in which the electron-emitting area is to be formed is formed, thereby applying the droplets to a predetermined position on the substrate;

a heat processing step of heat processing the applied liquid to form the electroconductive film; and

a an energization processing step of energization processing the electroconductive film,

wherein the liquid passes a liquid storage tank, a gas removing device and a temperature adjusting device sequentially in that order, and thereafter is introduced into a liquid discharge means operating in the ink jet manner.

30. (Previously Presented) An electron-emitting device manufacturing method according to claim 29, wherein the gas removal step comprises controlling a concentration of the gas dissolved in the liquid so as to be kept at a default value.

31. - 40. (Canceled)

41. (Previously Presented) An electron-emitting device manufacturing method according to claim 29, wherein, in the droplet discharge step, the droplet discharge means discharges the droplets of adjusted temperature in the ink jet manner onto a plurality of predetermined positions on the substrate, thereby applying the droplets to the predetermined positions on the substrate.

42. (Previously Presented) An electron-emitting device manufacturing method according to claim 41, wherein the gas removal step comprises controlling a concentration of the gas dissolved in the liquid so as to be kept at a default value.

43. - 48. (Canceled)

49. - 50. (Cancelled)